

Product Brief

Markets

- Internet of Things (IoT)
- Aerospace and defense
- WiFi
- Automotive
 - Skyworks offers AEC-Q101 qualified diodes
- Smart energy and connected home
- Cellular telephone infrastructure and handsets
- Remote meter reading for the smart grid
- Test and measurement
- Military communications
- Cable television (CATV)
- Point-to-point microwave radios
- Land mobile radio systems
- LTE
- Wearables



PIN, Limiter, Schottky, Varactor Diodes

Select diodes available from stock for prototype or high-volume production

Skyworks Solutions offers a select group of diodes from our diverse diode offering in stock and ready for immediate design into your demanding applications.

Select diodes include the most popular PIN, limiter, Schottky and tuning varactor diodes, readily available to ship from stock. These devices provide excellent performance and even better value for applications including smart energy, multiswitches, wireless local area networks (WLAN), cellular telephone networks, cable television (CATV), automotive, test and measurement equipment, land mobile radio and more.

PIN Diodes for Switch and Attenuator Applications

Part Number	Features	Markets
Switching PIN Diodes	S	
SMP1345-040LF	High isolation, fast switching	WLAN, infrastructure, general
SMP1320-040LF	Fast switching, high isolation, low insertion loss	WLAN, infrastructure, general
SMP1352-079LF	Large signal	Infrastructure, general
SMP1302-085LF	High power (50 W) handling, shunt	Land mobile radio, LTE base station, and more
SMP1325-087LF	High power (35 W) handling, series	Land mobile radio, LTE base station, and more
SMP1331-085LF	High power (50 W) handling, series	In frastructure, CATV, military, aeros pace and more and the contraction of the contrac

Attenuator PIN Diodes

SMP1304-085LF	Low capacitance, low distortion, single shunt	Infrastructure, CATV, military, aerospace and more
SMP1307-004LF	Low distortion / high IP3, dual	CATV, PON, base station, and more
SMP1307-027LF	Low distortion / high IP3, quad	CATV, PON, base station, and more



Join Our Customer Email Program Today

Skyworks is continually releasing new products. Join our customer email program instantly by scanning the QR code with your smartphone.

Skyworks Green™ products are compliant to all applicable materials legislation and are halogen-free. For additional information, please refer to Skyworks Definition of Green™, document number SQ04-0074.

Limiter Diodes for Receiver Protection Applications

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Part Number	Features	Markets
SMP1330-005LF	Clean-up limiter, +30 dBm input power, +13 dBm flat leakage power, up to 2.5 GHz	Land mobile radio, military, infrastructure, and more
SMP1330-085LF	Low loss, high power, +30 dBm input power, +13 dBm flat leakage power, up to 4 GHz	Land mobile radio, military, infrastructure, and more
CLA4603-085LF	Medium power, low loss, +33 dBm input power, +13 dBm flat leakage power, up to 10 GHz	Land mobile radio, military, infrastructure, and more
CLA4606-085LF	Medium power, low loss, +35 dBm input power, +18 dBm flat leakage power, up to 10 GHz	Land mobile radio, military, infrastructure, and more
CLA4609-086LF	Course limiter, high power handling, +43 dBm input power, +41 dBm flat leakage power, up to 6 GHz	Land mobile radio, military, infrastructure, and more
CLA4610-085LF	Medium power limiter, 16 dBm threshold, +39 dBm maximum power, operates up to 10 GHz	Infrastructure, WLAN, military and more
CLA4611-085LF	Medium power limiter, 25 dBm threshold, +40 dBm maximum power, operates up to 10 GHz	Land mobile radio, military, infrastructure, and more

Schottky Diodes for Detector and Mixer Applications

Part Number	Features	Markets
Detector Diodes		
SMS7621-060	Excellent sensitivity, low capacitance, 0201	WLAN, military, infrastructure, and more
SMS7621-040LF	Excellent sensitivity, low capacitance, 0402	WLAN, military, infrastructure, and more
SMS7621-005LF	Excellent sensitivity, low capacitance, series pair	Infrastructure, smart energy, infrastructure, and more
SMS7630-061	Best sensitivity, zero bias, 0201	WLAN, military, infrastructure, and more
SMS7630-040LF	Best sensitivity, zero bias, 0402	WLAN, military, infrastructure, and more
SMS3922-079LF	Medium barrier, high breakdown voltage	Infrastructure and more

Tuning Varactor Diodes for VCO, Voltage Tuned Filters and Phase Shifter Applications

Part Number	Features	Markets
Hyperabrupt Diodes		
SMV1234-040LF	Low capacitance (6.5 pF @1 V, 2 pF @ 6 V), low resistance (0.8 $\Omega)$	Automotive, smartenergy, WLAN, test and measuremen infrastructure, and more
SMV1232-040LF	High capacitance ratio at low reverse voltage: $C_{T_1}/C_{T_3} = 1.7$ typical	Automotive, smartenergy, WLAN, test and measurement infrastructure, and more
SMV1247-040LF	Low capacitance (7 pF @ 0.3 V, 0.7 pF @ 4.7 V), high Q (1500)	Automotive, smartenergy, WLAN, test and measuremen infrastructure, and more
SMV1249-079LF	Medium capacitance (31 pF @ 0.3 V, 2.6 pF @ 4.7 V)	Automotive, smartenergy, WLAN, test and measuremen infrastructure, and more
SMV1255-079LF	High capacitance (64 pF @ 0.3 V, 5.2 pF @ 4.7 V)	Automotive, smartenergy, WLAN, test and measuremen infrastructure, and more
SMV2201-040LF	Very low capacitance (0.85 pF @ 4 V), low phase noise	Automotive, smart energy, WLAN, test and measurement, infrastructure, and more
Abrupt Diodes		
SMV1405-040LF	Ultra high Q (3200)	Automotive, smartenergy, WLAN, test and measuremen infrastructure, and more
SMV1413-079LF	Low resistance, high Q	Automotive, smartenergy, WLAN, test and measuremen infrastructure, and more

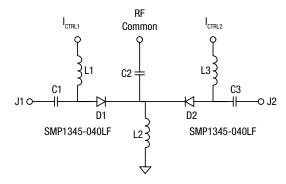
PIN Diodes

Features

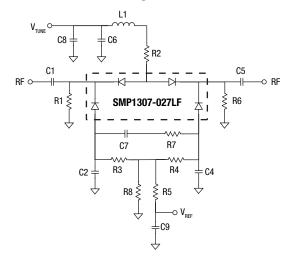
- Low capacitance for high isolation
- Low resistance
- Low distortion

Skyworks select PIN diodes are some of the most widely used PIN diodes in the world, for applications which range from RF switching in satellite television receiver low noise block converters (LNB) to automotive remote garage door openers to cable television automatic level controls.

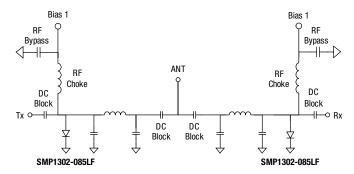
PIN diodes are three layer diodes, comprised of a heavily doped anode (the "P" layer) and a heavily doped cathode (the "N" layer) separated by a virtually undoped intrinsic layer (the "I" layer). Under forward bias, charge carriers from the P and the N layers are forced into the I layer, which reduces its RF impedance. When a reverse bias voltage is applied across the PIN diodes, all free charge carriers are removed from the I layer, thereby causing its RF impedance to increase. This variable RF impedance versus DC or low frequency bias signal allows the diode to be used in RF switching circuits, in which the PIN diode is either heavily forward-biased or reverse biased, or in RF attenuation circuits, in which case the PIN diode is utilized as a continuously-variable RF resistance by controlling the magnitude of the DC bias current through the diode.



Wide Bandwidth Single Pole Double Throw Switch



Wide Bandwidth PIN Diode Variable Attenuator



High Power SPDT PIN Switch

PIN Diodes for Switch and Attenuator Applications

Part Number	Product Description	Key Features	Package (mm)
SMP1345-040LF	High isolation, fast switching PIN diode	Very low capacitance (0.14 pF), isolation 40 dB	• 0402 1.0 x 0.60 x 0.46
SMP1320-040LF	Fast switching / high isolation, low insertion loss PIN diode	Low capacitance, low series resistance, small footprint	◆ 0402 1.0 x 0.60 x 0.46
SMP1352-079LF	Large signal switching PIN diode	Low capacitance, SC-79	SC-79 1.6 x 0.8 x 0.6
SMP1302-085LF	High power shunt PIN diode	Power handling to 50 W CW	◆ QFN 2 x 2 x 0.9
SMP1325-087LF	High power series PIN diode	Power handling to 34 W CW	QFN 2 x 2 x 0.9
SMP1307-004LF	Low distortion / high IP3 attenuator PIN diode	Low distortion common cathode configuration	SOT-23 2.37 x 2.92 x 1.0
SMP1307-027LF	Low distortion / high IP3 attenuator PIN diode	Low distortion, (4 diode) Pi configuration	SOT-5 2.8 x 2.9 x 1.8
SMP1304-085LF	High power shunt PIN diode	Power handling to 100 W CW	◆ QFN 2 x 2 x 0.9
SMP1331-085LF	High power shunt PIN diode	Power handling to 50 W CW	QFN 2 x 2 x 0.9

Receiver Protection Limiter Diodes

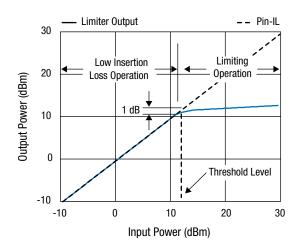
Features

- High power, mid-range cleanup designs
- Tight control of basewidth

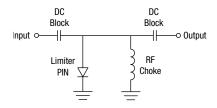
Skyworks' series of silicon limiter diode chips provides passive receiver protection over a wide range of frequencies from 100 MHz to beyond 30 GHz. These devices utilize Skyworks well established silicon technology for high resistivity and tightly controlled thin basewidth PIN limiter diodes. Limiter circuits employing these devices perform with strong limiting action and low loss.

The receiver protector function is performed by a specially processed PIN diode, known as a limiter diode. The PIN limiter diode can be described as an incident-powercontrolled, variable resistor. In the case when no large input signal is present, the impedance of the limiter diode is at its maximum, thereby producing minimum insertion loss, typically less than 0.5 dB. The presence of a large input signal temporarily forces the impedance of the diode to a much lower value, producing an impedance mismatch which reflects the majority of the input signal power back towards its source.

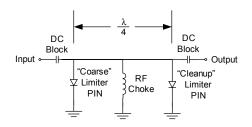
The input power level at which the limiter diode's impedance starts to decrease in response to a large input signal amplitude is primarily determined by the diode's I layer thickness. The diodes which "turn on" at the lowest signal levels have the thinnest I layers.



Output Power vs. Input Power for Single-Stage Limiter



Typical Single-Stage Limiter Circuit



Multistage Limiter Circuit

Limiter Diodes for Receiver Protection

Part Number	Product Description	Key Features	Package (mm)
SMP1330-005LF	Clean-up limiter, medium power handling	+9 dBm threshold level	SOT-23 2.37 x 2.92 x 1
SMP1331-085LF	Clean-up limiter, medium power handling	+9 dBm threshold level	QFN 2x2x0.9
CLA4603-085LF	Clean-up limiter, low loss, medium power handling	+9 dBm threshold level	QFN 2x2x0.9
CLA4606-085LF	Low loss, medium power handling	+10 dBm threshold level	QFN 2x2x0.9
CLA4609-086LF	Coarse limiter, high power handling	+38 dBm threshold level	QFN 2x2x0.9
CLA4610-085LF	High power limiter	+16 dBm threshold level	QFN 2 x 2 x 0.9
CLA4611-085LF	High power limiter	+25 dBm threshold level	QFN 2 x 2 x 0.9

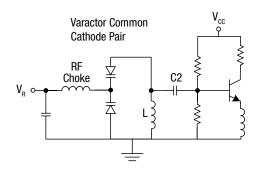
Tuning Varactor Diodes

Features

- Large available change in capacitance for wide bandwidth
- Low resistance for low loss

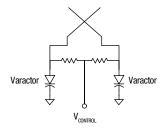
Skyworks series of select silicon tuning varactor diodes are used as the electrical tuning elements in voltage controlled oscillators (VCOs), voltage variable analog phase shifters and voltage tuned filters (VTFs). This family of diodes includes abrupt junction tuning varactors, useful for low loss, narrow band circuits, and hyperabrupt junction varactors, useful for wide bandwidth VCOs and VTFs and wide phase range variable phase shifters.

Tuning varactors are pn junction diodes. The depletion region that forms at the junction of the diode acts as a nearly-ideal insulator, which separates the highly-doped anode from the cathode layer, thus forming a parallel plate capacitor. The thickness of the depletion layer can be increased by applying a reverse bias voltage to the diode.

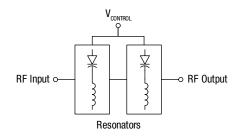


Typical Voltage Controlled Oscillator with a Common Cathode Pair of Tuning Varactors

The cathode layer's doping profile is very carefully designed to produce a tightly-controlled capacitance versus reverse bias voltage performance characteristic. The cathode layer of an abrupt junction diode has uniform dopant concentration throughout its thickness, which results in a low series resistance and moderately large change in capacitance versus bias voltage. By contrast, the doping concentration of cathode layer of hyperabrupt varactor diode is designed to change by several orders of magnitude, typically over the depth of a few microns. This non-constant dopant concentration versus depth of the hyperabrupt diode's cathode layer produces a much larger available change in capacitance versus reverse voltage, necessary for wide bandwidth or phase shift range applications.



Variable Phase Shifter



Voltage Tuned Filter

Tuning Varactor Diodes for VCO, Voltage Tuned Filters and Phase Shifter Applications

Part Number	Product Description	Key Feature	Package (mm)
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SMV1234-040LF	Low capacitance tuning varactor diode	Low capacitance (6.3 pF @ 1 V, 2 pF @ 6 V), low resistance (0.8 Ω) hyperabrupt	• 0402 1 x 0.6 x 0.46
SMV1232-040LF	Wide band width tuning varactor diode	High capacitance ratio at low reverse voltage: CT1/CT3 = 1.7 typical	• 0402 1 x 0.6 x 0.46
SMV1247-040LF	Low capacitance and high Qtuning varactor diode	Low capacitance (7 pF @ 0.3 V, 0.7 pF @ 4.7 V), high Q (1500) hyperabrupt	• 0402 1 x 0.6 x 0.46
SMV1249-079LF	Mediumcapacitanceandwidetuningrangediode	Medium capacitance (31 pF @ 0.3 V, 2.6 pF @ 4.7 V) hyperabrupt	SC-79 1.6 x 0.8 x 0.6
SMV1255-079LF	$High capacitan ce and wide tuning {\it range diode}$	High capacitance (64 pF @ 0.3 V, 5.2 pF @ 4.7 V) hyperabrupt	■ SC-79 1.6 x 0.8 x 0.6
SMV1405-040LF	Ultra high Q (3200) varactor for filter and VCO	Highest VB: 1.84 pF @ 1 V, 0.63 pF @ 30 V	• 0402 1 x 0.6 x 0.46
SMV1413-079LF	Low resistance and high Qabrupt tuning diode	Lowresistance (0.35 Ω), high Q (2400) and low capacitance (6.4 pF $@$ 1 V, 1.75 pF $@$ 30 V)	SC-79 1.6 x 0.8 x 0.6
SMV2201-040LF	Very low capacitance (0.85 pF @ 4 V), low phase noise	Low inductance (0.45 nH), low phase noise	• 0402 1 x 0.6 x 0.46

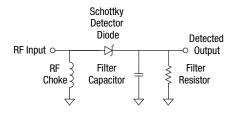
Schottky Diodes

Features

- Low capacitance for high frequency operation
- Excellent sensitivity
- High reverse breakdown voltage

Skyworks series of select silicon Schottky diodes are optimized for use as detector and mixer diodes at frequencies from below 10 MHz to higher than 20 GHz. This family of products includes medium, low and zero bias detector (ZBD) barrier height Schottky junctions with low junction capacitance and low series resistance.

Schottky junctions are formed by depositing specific metals on either n-type-doped silicon (low or medium barrier height) or on p-type-doped silicon (ZBD barrier height). The characteristics of the diode are determined by the type of metal deposited on the semiconductor material as well as the type of dopant in the semiconductor layer, among other parameters.



Single Schottky Diode Detector

Schottky Diodes for Detector and Mixer Applications

		•		
Part Number	Product Description	Key Features		Package (mm)
SMS7621-060	Mixerapplications up to 100 GHz and detector applications up to 40 GHz	Low barrier height, low inductance 0.15 nH, 0201 footprint	63	0201 0.60 x 0.30 x 0.27
SMS7621-040LF	Detector Schottky diode	Low barrier height and low capacitance	•	0402 1.0 x 0.60 x 0.46
SMS7621-005LF	Series pair detector Schottky diodes	Low barrier height and low capacitance	-	SOT-23 2.37 x 2.92 x 1.0
SMS7630-061	Detector applications up to 40 GHz	Lowest barrier height, low inductance 0.15 nH, 0201 footprint	ija)	0201 0.60 x 0.30 x 0.27
SMS7630-040LF	Zerobiased detector Schottky dio de	Lowest barrier height for best sensitivity	•	0402 1.0 x 0.60 x 0.46
SMS3922-079LF	Medium barrier detector Schottky diode	Mediumbarrierheightwithhighbreakdownvoltage(>8volts)	*	SC-79 1.6 x 0.8 x 0.6



USA

Headquarters: Massachusetts

Skyworks Solutions 20 Sylvan Road Woburn, MA 01801 Telephone: (781) 376-3000 Fax: (781) 376-3100 sales@skyworksinc.com

California

Skyworks Solutions 5221 California Avenue Irvine, CA 92617 Telephone: (949) 231-3000 Fax: (949) 231-3206 sales@skyworksinc.com

Skyworks Solutions 3230 Scott Boulevard Santa Clara, CA 95054 Telephone: (408) 330-1400 Fax: (408) 737-4611 sales@skyworksinc.com

EUROPE

France

Skyworks Solutions 60 rue Saint André des Arts Bâtiment D 75006 Paris France Telephone: +33 1 43548540 Fax: +33 1 43540005 irene.pfeiffer@skyworksinc.com

United Kingdom

Skyworks Solutions Ground Floor, Riverside House Riverside Bishop's Stortford Herts CM23 3AJ **United Kingdom** Telephone: +44 7920 838883 will.kerley@skyworksinc.com

Finland **Skyworks Solutions**

Keilaranta 16 (5th Floor) FIN-02150 Espoo Finland Telephone: +358 9251 07131 Fax: +358 9 2510 7129 tommi.hiillos@skyworksinc.com

ASIA • PACIFIC

China

Skyworks Solutions Room 2901-02, Chong Hing Finance Center No. 288 Nanjing Road (W) Shanghai 200003 China PRC Telephone: +86 21 23066230 ext. 60167 Fax: +86 21 33663398 elaine.zhao@skyworksinc.com

Skyworks Solutions Room 2701, 27/F Tower 3 Kerry Plaza No. 1 Zhongxinsi Road **Futian District** Shenzhen 518048 China PRC Telephone: +86 755 8828 8399 Fax: +86 755 8828 8358 jesse.li@skyworksinc.com

Skyworks Solutions Suite 1315, Tower B, COFCO Plaza, No. 8 Jianguomennei Avenue Dongcheng District Beijing 100005 China PRC Telephone: +8610 652 60859 ext. 61602 Fax: +8610 652 61358 abby.huang@skyworksinc.com

Japan

Skyworks Solutions Tokyo Opera City Tower 36F 3-20-2 Nishi-Shinjuku Shinjuku-ku Tokyo, 163-1436 Japan Telephone: +81 3 5308 5180 Fax: +81 3 5308 5190 ahihiro.karikomi@skyworksinc.com

Skyworks Solutions POSCO Center (West Wing 12F) 440 Taeheran-ro, Gangnam-ku Seoul, 06194, Korea Telephone: +82 2 3490 3800 Fax: +82 2 553 5459 juhee.lee@skyworksinc.com

Singapore

Skyworks Solutions 10 Ang Mo Kio Street 65 #05-15/16 Techpoint Singapore 569059 Telephone: +65 64031971 Fax: +65 64031931 yuenfong.choong@skyworksinc.com

Taiwan

Skyworks Solutions 4 F, #198, Section 2 Tun Hwa S. Road Taipei 106, Taiwan ROC Telephone: +8862 5559 8992 Fax: +8662 2735 6508 joanna.wu@skyworksinc.com



For the latest information, please visit our website at <u>www.skyworksinc.com</u>

